

#### **DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**

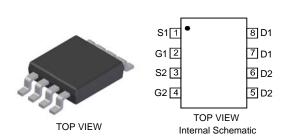
#### **Features**

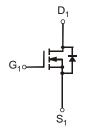
- Dual N-Channel MOSFET
- Low On-Resistance
  - $22m\Omega$  @  $V_{GS} = 10V$
  - $33m\Omega$  @  $V_{GS} = 4.5V$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 4)
- Qualified to AEC-Q101 Standards for High Reliability

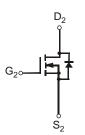
#### **Mechanical Data**

- Case: SOP-8L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame.
  Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072grams (approximate)

SOP-8L







N-Channel MOSFET

N-Channel MOSFET

### Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Chara	cteristic		Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Drain Current (Note 1)	Steady State	$T_A = 25$ °C $T_A = 70$ °C	I <sub>D</sub>	6.9 5.8	А
Pulsed Drain Current (Note 3)			I <sub>DM</sub>	30	А

### Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	$P_{D}$	2	W
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	62.5	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

Notes:

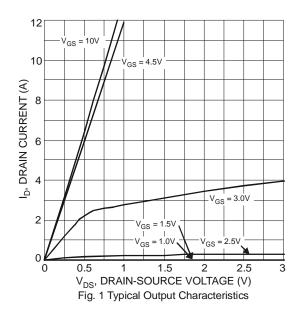
- 1. Device mounted on 2 oz. Copper pads on FR-4 PCB with  $R_{0JA}$  = 62.5°C/W
- 2. No purposefully added lead.
- 3. Pulse width  $\leq 10 \mu S$ , Duty Cycle  $\leq 1\%$ .
- 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

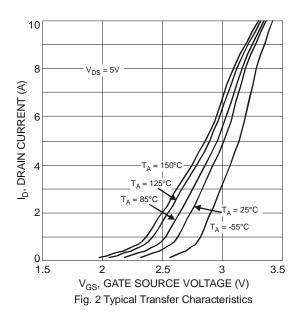


## Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

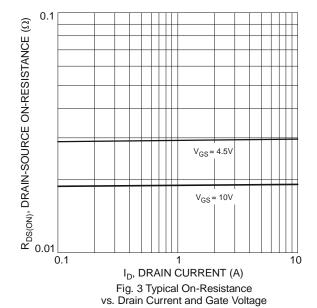
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μА	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)					ā.	
Gate Threshold Voltage	V <sub>GS(th)</sub>	1		2.1	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	D (211)		_	22	mΩ	$V_{GS} = 10V, I_D = 6.9A$
Static Dialit-Source Off-Resistance	R <sub>DS</sub> (ON)			33	1115.2	$V_{GS} = 4.5V, I_D = 5.0A$
Forward Transconductance	<b>g</b> fs	_	7	_	S	$V_{DS} = 5V$ , $I_{D} = 6.9A$
Diode Forward Voltage (Note 5)	$V_{SD}$	0.5	_	1.2	V	$V_{GS} = 0V, I_{S} = 1A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	Ciss	_	725	_	pF	151/1/
Output Capacitance	Coss	_	114	_	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V -f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	92	_	pF	-1 = 1:0W112
Gate Resistance	$R_{G}$	_	0.89	_	Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz$
SWITCHING CHARACTERISTICS						
Total Gate Charge	$Q_g$		6.4		nC	$V_{GS} = 4.5V, V_{DS} = 15V, I_{D} = 5A$
Total Cate Ollarge	Qg		13.0		110	$V_{GS} = 10V, V_{DS} = 15V, I_D = 6.9A$
Gate-Source Charge	$Q_{gs}$	_	1.9	_	nC	$V_{GS} = 4.5V$ , $V_{DS} = 15V$ , $I_{D} = 6.9A$
Gate-Drain Charge	$Q_{gd}$	_	3.2	_	nC	$V_{GS} = 4.5V, V_{DS} = 15V, I_D = 6.9A$
Turn-On Delay Time	t <sub>d(on)</sub>	_	11	_	ns	
Turn-On Rise Time	t <sub>r</sub>	_	7	_	ns	$V_{DD} = 15V, V_{GS} = 10V,$
Turn-Off Delay Time	t <sub>d(off)</sub>	_	63	_	ns	$R_D = 1.8\Omega$ , $R_G = 6\Omega$
Turn-Off Fall Time	t <sub>f</sub>	_	30	_	ns	

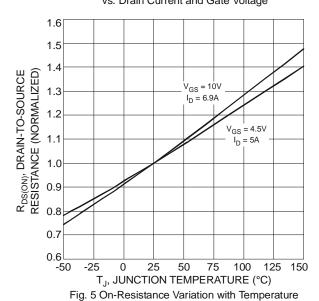
Notes: 5. Short duration pulse test used to minimize self-heating effect.

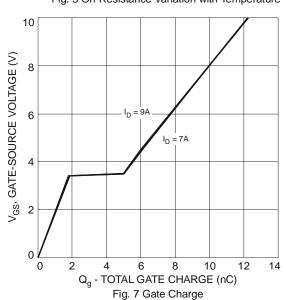












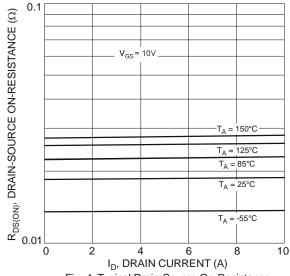
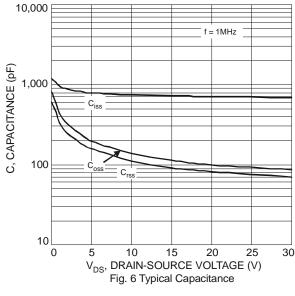


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature



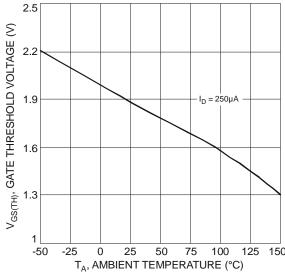


Fig. 8 Gate Threshold Variation vs. Ambient Temperature



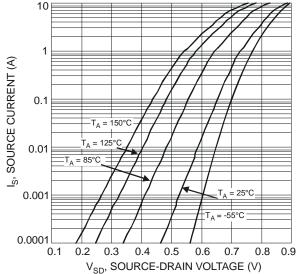


Fig. 9 Diode Forward Voltage vs. Current

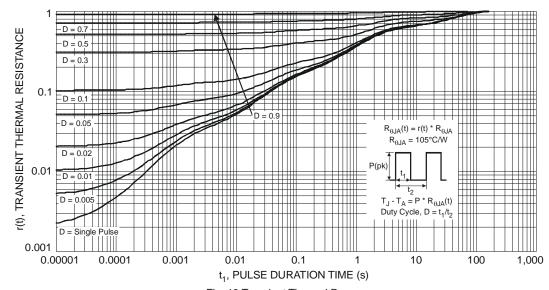


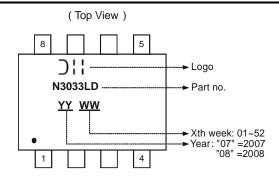
Fig. 10 Transient Thermal Response

## Ordering Information (Note 6)

ſ	Part Number	Case	Packaging
	DMN3033LSD-13	SOP-8L	2500/Tape & Reel

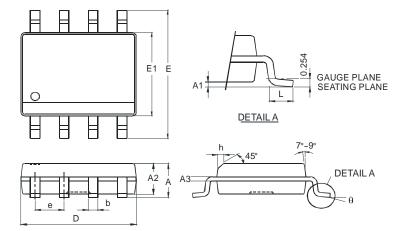
Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**



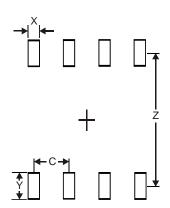


## **Package Outline Dimensions**



SOP-8L				
Dim	Min	Max		
Α	-	1.75		
A1	0.08	0.25		
A2	1.30	1.50		
A3	0.20 Typ.			
b	0.3	0.5		
D	4.80	5.30		
Е	5.79	6.20		
E1	3.70	4.10		
е	1.27 Typ.			
h	-	0.35		
L	0.38	1.27		
θ	0°	8°		
All Dimensions in mm				

## **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	5.1
С	1.27
X	0.41
Y	1.0



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